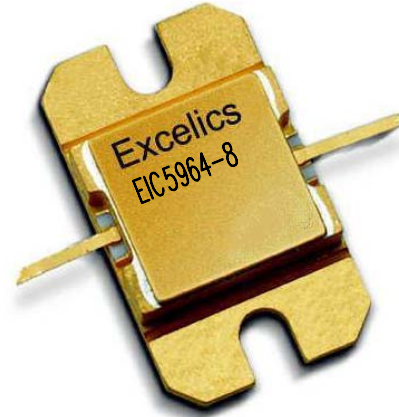


5.90-6.40 GHz 8-Watt Internally-Matched Power FET

FEATURES

- 5.90 – 6.40 GHz Bandwidth
- Input/Output Impedance Matched to 50 Ohms
- +39.5 dBm Output Power at 1dB Compression
- 10.0 dB Power Gain at 1dB Compression
- 37% Power Added Efficiency
- -46 dBc IM3 at $P_o = 28.5$ dBm SCL
- Hermetic Metal Flange Package
- 100% Tested for DC, RF, and R_{TH}



DESCRIPTION

The EIC5964-8 is a high power, highly linear, single stage MFET amplifier in a flange mount package. This amplifier features Excelics' unique MESFET transistor technology.



Caution! ESD sensitive device.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETERS/TEST CONDITIONS ¹	MIN	TYP	MAX	UNITS
P_{1dB}	Output Power at 1dB Compression $f = 5.90\text{-}6.40\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 2200\text{mA}$	38.5	39.5		dBm
G_{1dB}	Gain at 1dB Compression $f = 5.90\text{-}6.40\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 2200\text{mA}$	9	10		dB
ΔG	Gain Flatness $f = 5.90\text{-}6.40\text{GHz}$ $V_{DS} = 10\text{ V}, I_{DSQ} \approx 2200\text{mA}$			± 0.6	dB
PAE	Power Added Efficiency at 1dB Compression $V_{DS} = 10\text{ V}, I_{DSQ} \approx 2200\text{mA}$ $f = 5.90\text{-}6.40\text{GHz}$		37		%
I_{d1dB}	Drain Current at 1dB Compression $f = 5.90\text{-}6.40\text{GHz}$		2200	2600	mA
IM3	Output 3rd Order Intermodulation Distortion $\Delta f = 10\text{ MHz}$ 2-Tone Test; $P_{out} = 28.5\text{ dBm}$ S.C.L. ² $V_{DS} = 10\text{ V}, I_{DSQ} \approx 65\% I_{DSS}$ $f = 6.40\text{ GHz}$	-43	-46		dBc
I_{DSS}	Saturated Drain Current $V_{DS} = 3\text{ V}, V_{GS} = 0\text{ V}$		4000	4500	mA
V_P	Pinch-off Voltage $V_{DS} = 3\text{ V}, I_{DS} = 40\text{ mA}$		-2.5	-4.0	V
R_{TH}	Thermal Resistance ³		3.5	4.0	$^\circ\text{C/W}$

Notes:

1. Tested with 100 Ohm gate resistor.
2. S.C.L. = Single Carrier Level.
3. Overall R_{th} depends on case mounting.



EIC5964-8

ABSOLUTE MAXIMUM RATINGS FOR CONTINUOUS OPERATION^{1,2}

SYMBOL	CHARACTERISTIC	VALUE
V _{DS}	Drain to Source Voltage	10 V
V _{GS}	Gate to Source Voltage	-4.5 V
I _{DS}	Drain Current	IDSS
I _{GSF}	Forward Gate Current	80 mA
P _{IN}	Input Power	@ 3dB compression
P _T	Total Power Dissipation	32 W
T _{CH}	Channel Temperature	150°C
T _{STG}	Storage Temperature	-65/+150°C

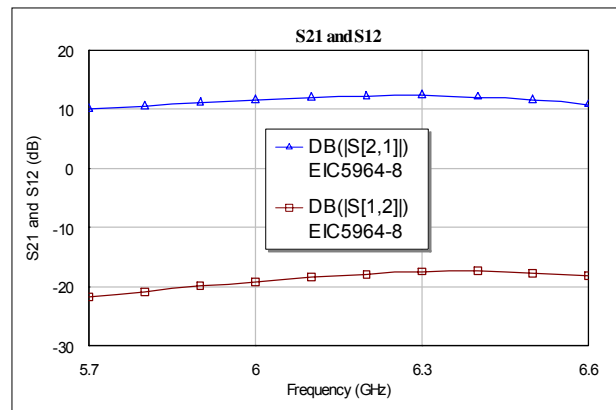
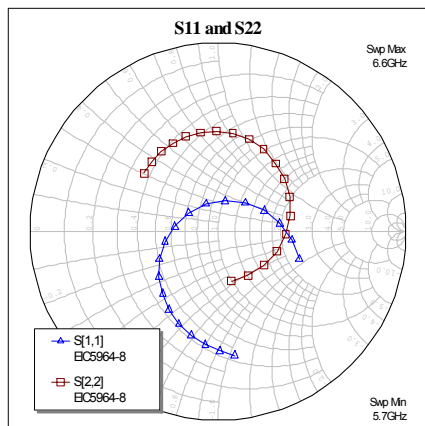
Notes:

- Operating the device beyond any of the above ratings may result in permanent damage or reduction of MTTF.
- Bias conditions must also satisfy the following equation $P_T < (T_{CH} - T_{PKG})/R_{TH}$; where T_{PKG} = temperature of package, and $P_T = (V_{DS} * I_{DS}) - (P_{OUT} - P_{IN})$.

PERFORMANCE DATA

Typical S-Parameters (T= 25°C, 50Ω system, de-embedded to edge of package)

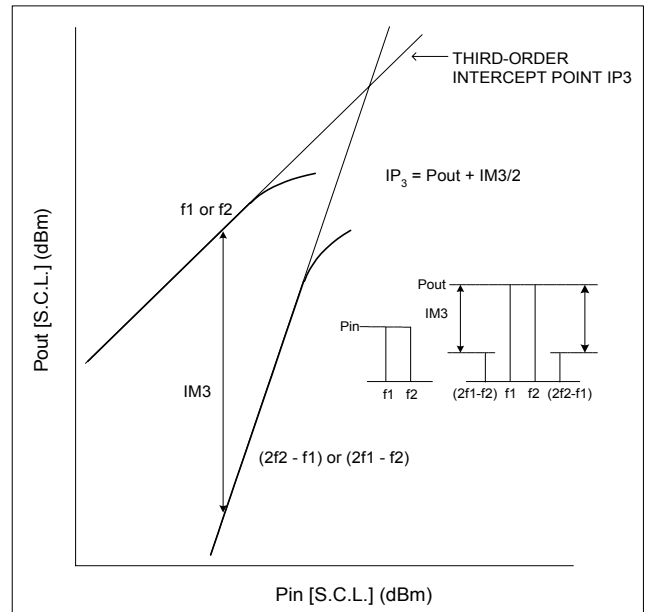
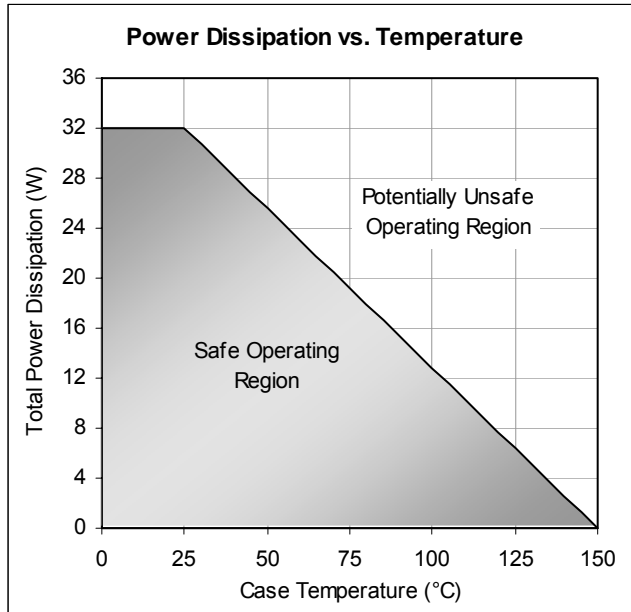
V_{DS} = 10 V, I_{DSQ} ≈ 2200mA



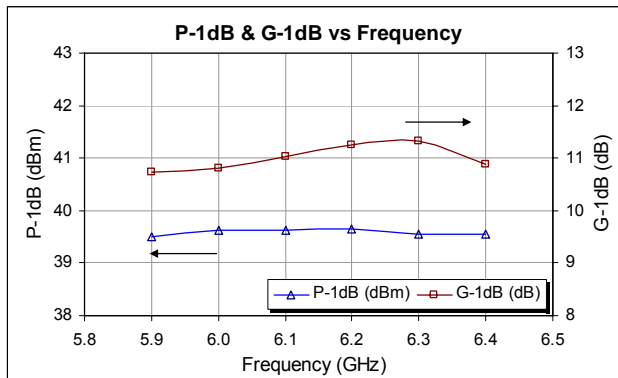
FREQ (GHz)	--- S11 ---		--- S21 ---		--- S12 ---		--- S22 ---	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
5.0	0.873	-7.73	1.9865	102.43	0.0385	50.45	0.4069	-90.78
5.2	0.8439	-25.93	2.285	77.92	0.0467	23.43	0.4003	-128.98
5.4	0.7893	-46.35	2.6094	51.4	0.0592	-4.16	0.4285	-166.69
5.6	0.7151	-69.29	2.9628	23.77	0.0737	-33.07	0.4765	158.39
5.8	0.6028	-96.47	3.3734	-5.88	0.0912	-62.69	0.5213	125.52
6.0	0.444	-131.54	3.7964	-39.07	0.1107	-96.25	0.5321	90.88
6.2	0.2308	173.31	4.0744	-76.09	0.1282	-133.24	0.4733	49.87
6.4	0.2091	46.37	4.0033	-116.4	0.1362	-173.52	0.3603	-2.01
6.6	0.455	-18.8	3.4617	-156.9	0.1237	147.8	0.2712	-75.07
6.8	0.6333	-56.77	2.6951	167.51	0.1009	112.66	0.3134	-142.54
7.0	0.7311	-85.42	2.035	136.97	0.0814	83.64	0.4055	176.45

Specifications are subject to change without notice.

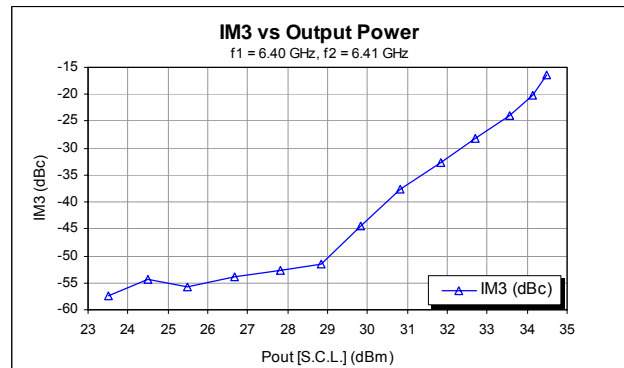
Power De-rating Curve and IM3 Definition



Typical Power Data ($V_{DS} = 10$ V, $I_{DSQ} = 2200$ mA)

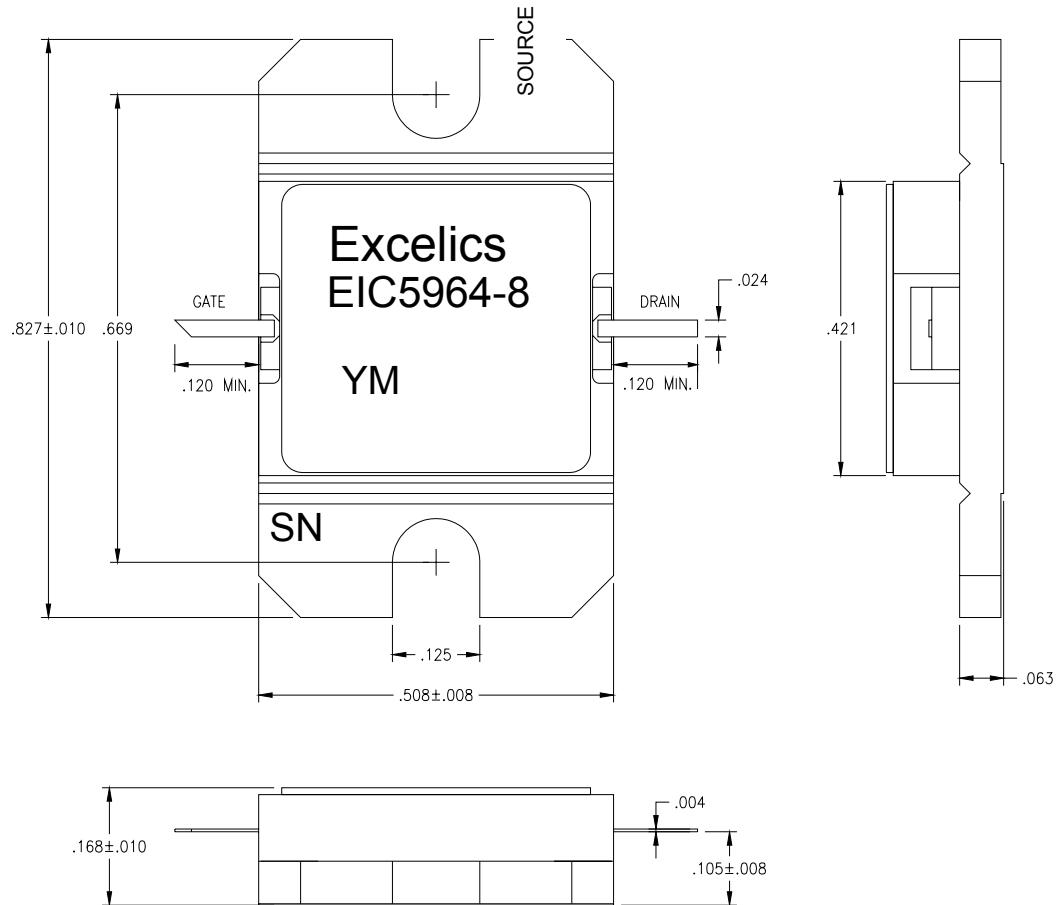


Typical IM3 Data ($V_{DS} = 10$ V, $I_{DSQ} \approx 65\%$ IDSS)



PACKAGE OUTLINE

Dimensions in inches, Tolerance $\pm .005$ unless otherwise specified



ORDERING INFORMATION

Part Number	Grade ¹	f_{Test} (GHz)	$P_{1\text{dB}}$ (min)	IM_3 (min) ²
EIC5964-8	Industrial	5.9-6.4 GHz	38.5	-43

- Notes:
1. Contact factory for military and hi-rel grades.
 2. Exact test conditions are specified in "Electrical Characteristics" table.